

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes a non-single-crystal semiconductor film, a support substrate that supports the non-single-crystal semiconductor film, and an active device having a part of the non-single-crystal semiconductor film as a channel region.

In particular, the channel region has an oxygen concentration not higher than  $1 \times 10^{18}$  atoms/cm<sup>3</sup> and a carbon concentration not higher than  $1 \times 10^{18}$  atoms/cm<sup>3</sup>.